

500V N-CHANNEL ENHANCEMENT MODE MOSFET

MAIN CHARACTERISTICS

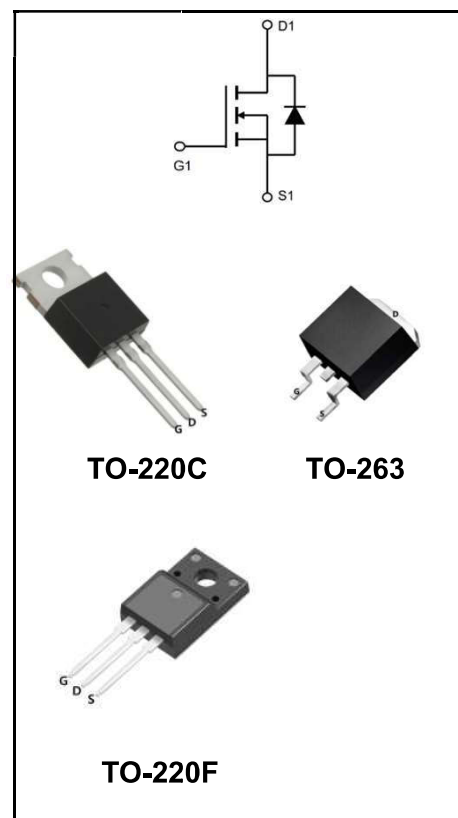
I_D	10A
V_{DSS}	500V
$R_{DS(on)}=typ(@V_{GS}=10V)$	$<0.68\Omega$ (Type: 0.56 Ω)

Features

- ♦Fast Switching
- ♦Low ON Resistance
- ♦Low Gate Charge
- ♦100% Single Pulse avalanche energy Test
- ♦LeadfreeincomplywithEU RoHS2011/65/EU directives

Mechanical Data

- ♦Case: Molded plastic
- ♦Mounting Position: Any
- ♦Molded Plastic: UL Flammability Classification Rating 94V-0
- ♦Solder bath temperature 275°C maximum, 10s per JESD22-106



Product Specification Classification

Part Number	Package	Marking	Pack
YFW10N50AC	TO-220C	YFW 10N50AC XXXXX	50PCS/Tube
YFW10N50AF	TO-220F(0.5mm)	YFW 10N50AF XXXXX	50PCS/Tube
YFW10N50AF	TO-220F(1.3mm)	YFW 10N50AF XXXXX	50PCS/Tube
YFW10N50AS	TO-263	YFW 10N50AS XXXXX	50PCS/Tube
YFW10N50AS-R	TO-263	YFW 10N50AS XXXXX	800PCS/Tape

Maximum Ratings at Tc=25°C unless otherwise specified

Characteristics	Symbols	Value			Units
		220C	220F	263	
Drain-Source Voltage	V _{DS}	500			V
Gate-Source Voltage	V _{GS}	±30			V
Continue Drain Current-Continuous (TC = 25°C)	I _D	10			A
-Continuous (TC = 100°C)		6			
Pulsed Drain Current (Note1)	I _{DM}	40			A
Power Dissipation	P _D	143	48	140	W
-Derate above 25°C		1.14	0.38	1.14	W/°C
Single Pulse Avalanche Energy (Note2)	E _{AS}	650			mJ
Avalanche Current (Note 1)	I _{AR}	10			A
Repetitive Avalanche Energy (Note 1)	E _{AS}	14			mJ
Operating Temperature Range	T _J	150			°C
Storage Temperature Range	T _{STG}	-55 to +150			°C
Thermal Resistance, Junction to Case	R _{θJC}	0.92	2.68	0.92	°C/W
Thermal Resistance, Junction to Ambient	R _{θJA}	62.5	62.5	62.5	°C/W

Maximum Ratings at Tc=25°C unless otherwise specified

Characteristics	Test Condition	Symbols	Min	Typ	Max	Units
Drain-Source Breakdown Voltage	$V_{GS} = 0\text{ V}, I_D = 250\text{ }\mu\text{A}$	BV_{DSS}	500	-	-	V
Drain-Source Leakage Current	$V_{DS} = 500\text{ V}, V_{GS} = 0\text{ V}$	I_{DSS}	-	-	1	μA
	$V_{DS} = 400\text{ V}, T_c = 125^\circ\text{C}$		-	-	10	
Gate Leakage Current	$V_{GS} = \pm 30\text{ V}, V_{DS} = 0\text{ V}$	I_{GSS}	-	-	± 100	nA
Gate-Source Threshold Voltage	$V_{DS} = V_{GS}, I_D = 250\text{ }\mu\text{A}$	$V_{GS(th)}$	2	-	4	V
Drain-Source On-State Resistance	$V_{GS} = 10\text{ V}, I_D = 5\text{ A}$	$R_{DS(on)}$	-	0.56	0.68	Ω
Forward Transconductance(Note3)	$V_{DS} = 40\text{ V}, I_D = 5\text{ A}$	g_{fs}	-	10	-	S
Input Capacitance	$V_{GS} = 0\text{ V}, V_{DS} = 25\text{ V}, f = 1\text{ MHz}$	C_{iss}	-	1100	-	pF
Output Capacitance		C_{oss}	-	156	-	
Reverse Transfer Capacitance		C_{rss}	-	7	-	
Turn-on Delay Time	$I_D = 10\text{ A}, V_{DD} = 250\text{ V}, R_G = 25\Omega(\text{Note3,4})$	$t_d(ON)$	-	25	-	nS
Rise Time		t_r	-	20	-	
Turn-Off Delay Time		$t_d(OFF)$	-	50	-	
Fall Time		t_f	-	20	-	
Total Gate Charge	$I_D = 10\text{ A}, V_{DD} = 400\text{ V}, V_{GS} = 10\text{ V}(\text{Note3,4})$	Q_G	-	32	-	nC
Gate to Source Charge		Q_{GS}	-	8	-	
Gate to Drain Charge		Q_{GD}	-	12	-	

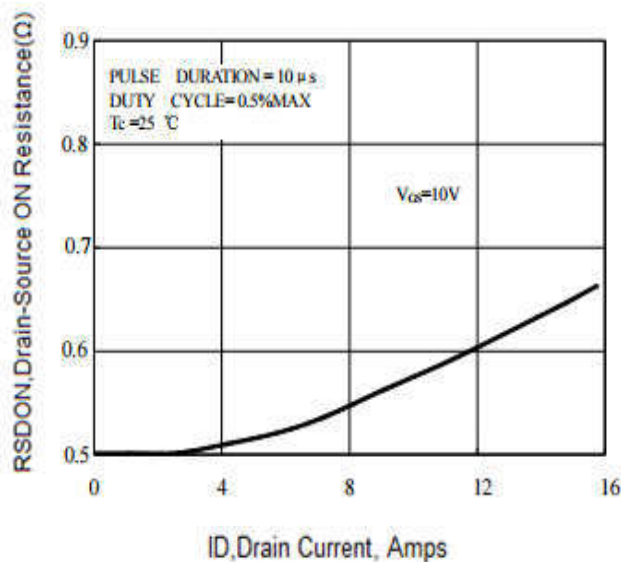
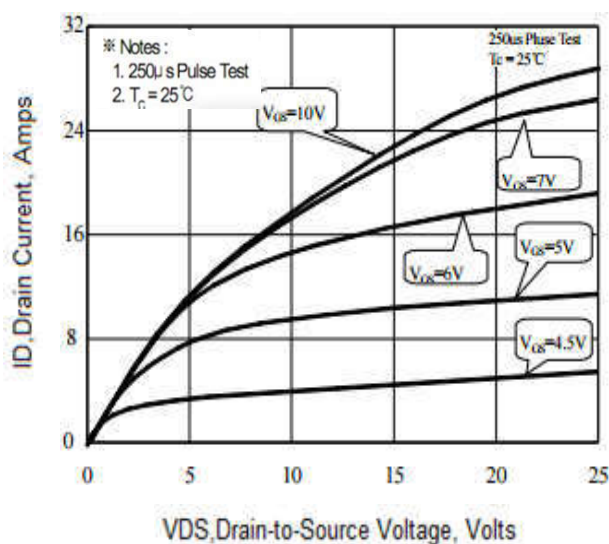
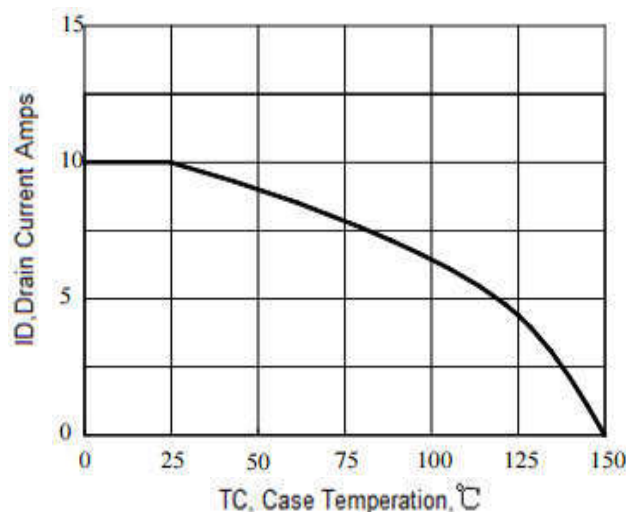
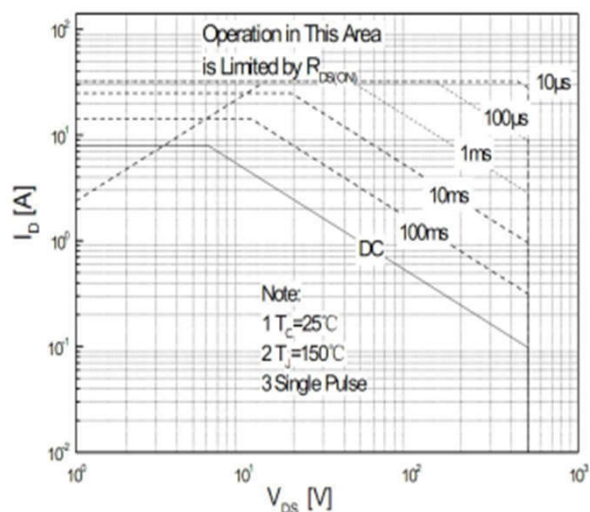
Source-Drain Diode Characteristics at Ta=25°C unless otherwise specified

Characteristics	Test Condition	Symbols	Min	Typ	Max	Units
Maximum Continuous Drain-Source Diode Forward Current		I_S	-	-	10	A
Maximum Pulsed Drain-Source Diode Forward Current		I_{SM}	-	-	40	A
Drain-Source Diode Forward Voltage	$I_{SD} = 10\text{ A}$	V_{SD}	-	-	1.4	V
Reverse Recovery Time	$I_{SD} = 10\text{ A}$, $V_{GS} = 0\text{ V}$, $dI_F / dt = 100\text{ A}/\mu\text{s}$ (Note3)	t_{rr}	-	398	-	nS
Reverse Recovery Charge		Q_{rr}	-	2.5	-	uC

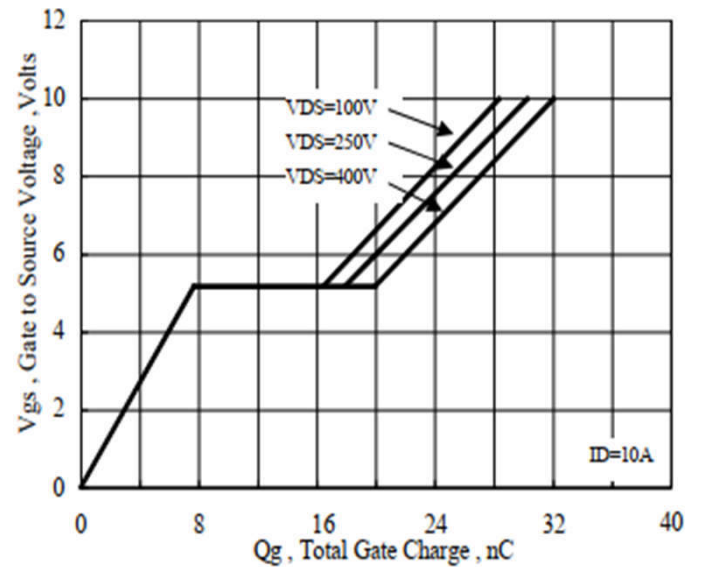
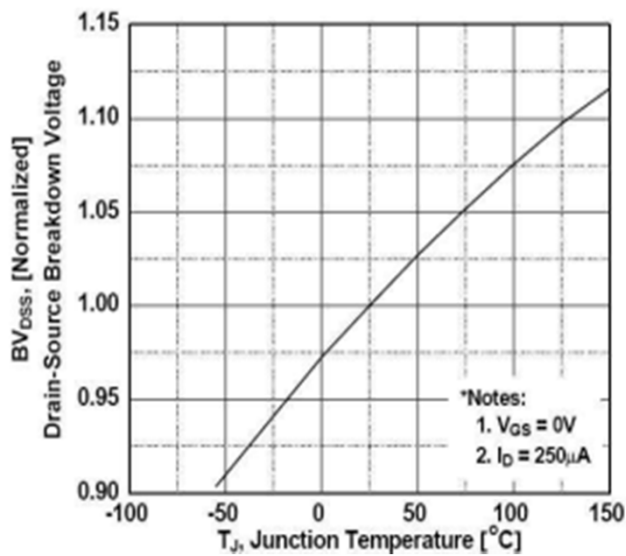
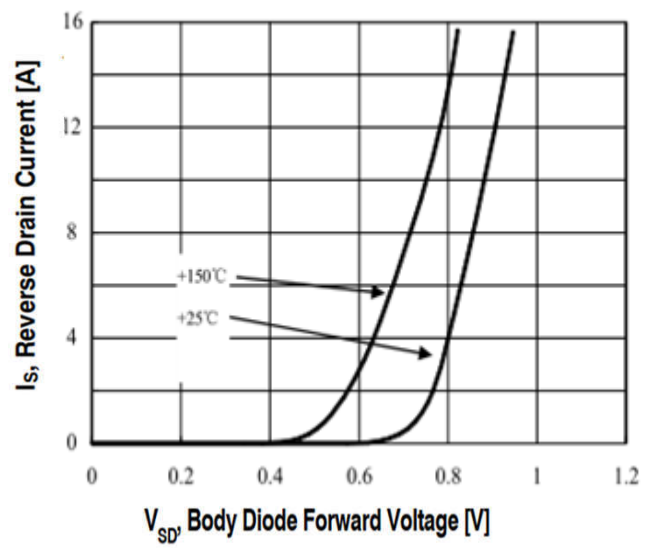
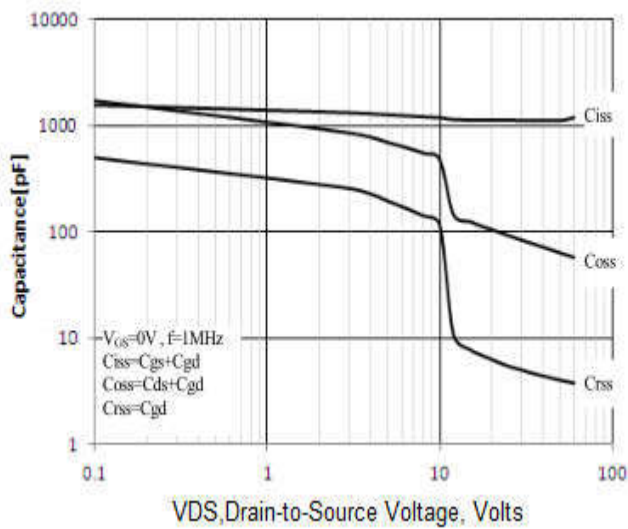
Note:

1. Repetitive Rating: Pulse width limited by maximum junction temperature.
2. $I_{AS} = 10\text{ A}$, $V_{DD} = 50\text{ V}$, $L = 12\text{mH}$, $R_G = 25\Omega$, starting $T_J = 25^\circ\text{C}$.
3. ulse test: Pulse Width $\leq 300\text{ }\mu\text{s}$, Duty Cycle $\leq 2\%$.
4. Essentially Independent of Operating Temperature.

Ratings and Characteristic Curves



Ratings and Characteristic Curves



Package Outline Dimensions Millimeters
TO-220C

The image shows a technical drawing of a TO-220C package. It includes a front view and a side view. The front view shows the package with dimensions A, A2, F, E, G, J, D, M, N, and S. The side view shows dimensions C, C1, P, and H. The package has a central pin and two side pins. The dimensions are labeled in millimeters.

Dim.	Min.	Max.
A	9.8	10.2
A2	4.8	5.2
C	4.35	4.65
C1	1.45	1.05
D	0.65	0.95
E	3.45	3.75
F	2.85	3.15
G	6.4	6.8
H	0.35	0.65
J	28.68	28.98
K	2.8	3.2
M	1.15	1.45
N	Typical 2.54	
P	2.2	2.6
Q	9	9.4
S	0.15	0.35
U	2.65	2.95
DIA	宽 1.50 ± 0.10	
	深 0.50 MAX	

All Dimensions in millimeter

TO-220F

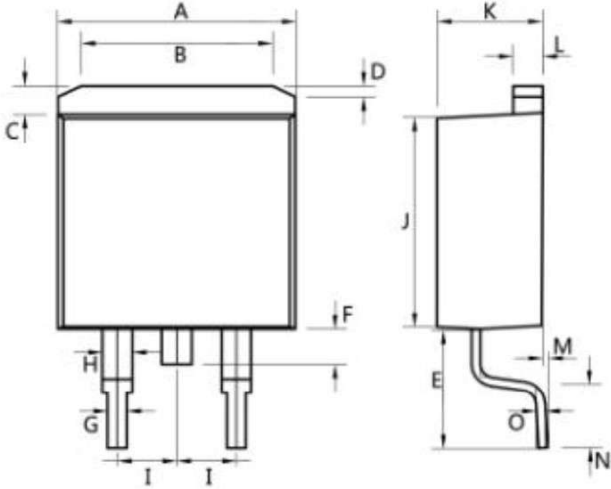
The image shows a technical drawing of a TO-220F package. The front view (left) shows a rectangular body with a central circular feature and four mounting holes. Dimensions A, B, C, D, F, G, H, and I are labeled. The side view (right) shows the profile of the package, including the mounting tab and the lead. Dimensions J, K, L, M, N, and Q are labeled.

Dim.	Min.	Max.
A	9.95	10.25
B	2.95	3.25
C	1.25	1.45
D	12.95	13.25
E	0.50	0.65
F	3.1	3.3
G	1.30	1.45
H	Typ 2.54	
I	Typ 5.08	
J	4.60	4.75
K	2.50	2.65
L	6.35	6.55
M	15.4	16.0
N	2.75	3.05
O	0.48	0.52
P	0.76	0.84

All Dimensions in millimeter

Package Outline Dimensions Millimeters

TO-263

	Dim.	Min.	Max.
	A	10.1	10.2
	B	7.4	7.6
	C	1.3	1.5
	D	0.55	0.75
	E	5.0	6.0
	F	1.4	1.6
	G	0.78	0.86
	H	1.2	1.3
	I	Typ2.54	
	J	8.4	8.6
	K	4.45	4.55
	L	1.25	1.35
	M	0.02	0.1
	N	2.4	2.8
	O	0.36	0.40
All Dimensions in millimeter			